Silicon Carbide (SiC) Schottky Diode – EliteSiC, 12 A, 650 V, D1, D2PAK-2L

FFSB1265A

1, 3 Cathode   2 Anode

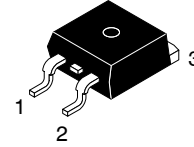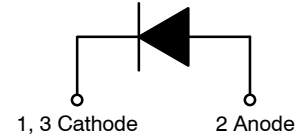**D2PAK−2L (TO−263−2L)**
CASE 418BK

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 72 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
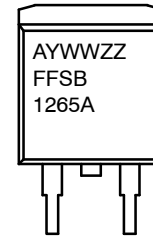- This Device is Pb−Free, Halogen Free/BFR Free and RoHS Compliant

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

MARKING DIAGRAM

AYWWZZ
FFSB
1265A

A	= Assembly Plant Code
YWW	= Data code (Year & Week)
ZZ	= Lot Code
FFSB1265A	= Specific Device Code

ORDERING INFORMATION

FFSB1265A

ABSOLUTE MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{RRM}	Peak Repetitive Reverse Voltage		650	V
E_{AS}	Single Pulse Avalanche Energy (Note 1)		72	mJ
I_F	Continuous Rectified Forward Current @ T_C < 143°C		12	A
	Continuous Rectified Forward Current @ T_C < 135°C		14	A
$I_{F, Max}$	Non-Repetitive Peak Forward Surge Current	T_C = 25°C, 10 μs	940	A
		T_C = 150°C, 10 μs	890	A
$I_{F, SM}$	Non−Repetitive Forward Surge Current	Half−Sine Pulse, t_p = 8.3 ms	70	A
$I_{F, RM}$	Repetitive Forward Surge Current	Half−Sine Pulse, t_p = 8.3 ms	43	A
P_{tot}	Power Dissipation	T_C = 25°C	100	W
		T_C = 150°C	17	W
T_J, T_{STG}	Operating and Storage Temperature Range		−55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	1.5	°C/W

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Shipping[†]
FFSB1265A	FFSB1265A	D2PAK−2L (TO−263−2L)	Tape and Reel	330 mm	24 mm	800 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ON WAFER (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V_F	Forward Voltage	I_F = 12 A, T_C = 25°C	–	1.50	1.75	V
		I_F = 12 A, T_C = 125°C	–	1.60	2.0	
		I_F = 12 A, T_C = 175°C	–	1.72	2.4	
I_R	Reverse Current	V_R = 650 V, T_C = 25°C	–	–	200	μA
		V_R = 650 V, T_C = 125°C	–	–	400	
		V_R = 650 V, T_C = 175°C	–	–	600	
Q_C	Total Capacitive Charge	V = 400 V	–	40	–	nC
C	Total Capacitance	V_R = 1 V, f = 100 kHz	–	665	–	pF
		V_R = 200 V, f = 100 kHz	–	74	–	
		V_R = 400 V, f = 100 kHz	–	54	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:
1. E_{AS} of 72 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 17 A, V = 50 V.

TYPICAL CHARACTERISTICS
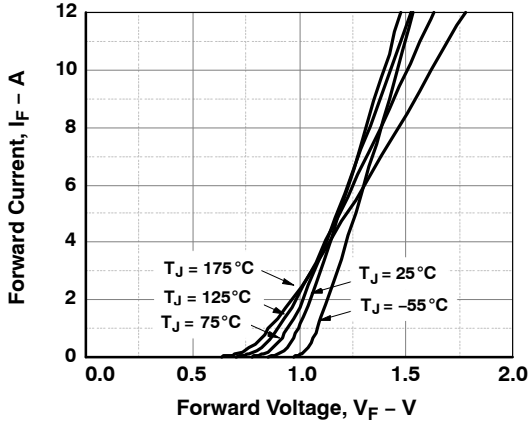
(T_J = 25°C UNLESS OTHERWISE NOTED)
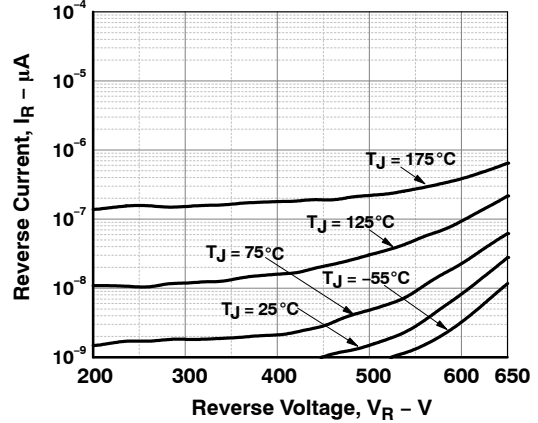

Figure 1. Forward Characteristics

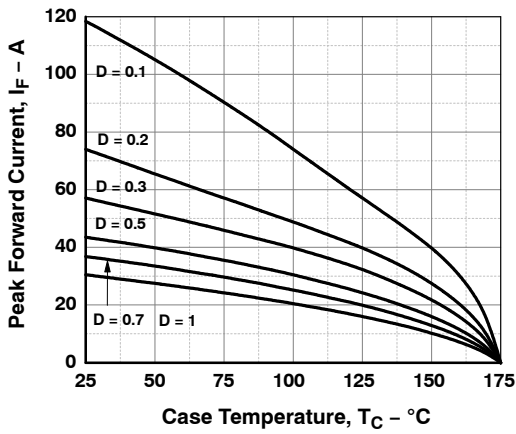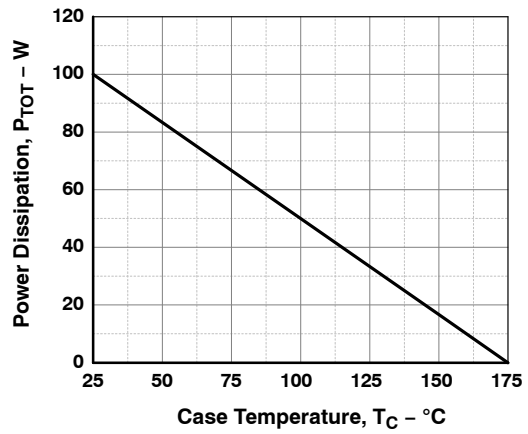Figure 2. Reverse Characteristics

Figure 3. Current Derating

Figure 4. Power Derating
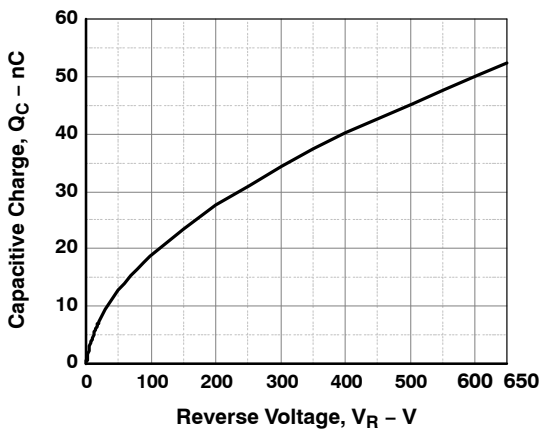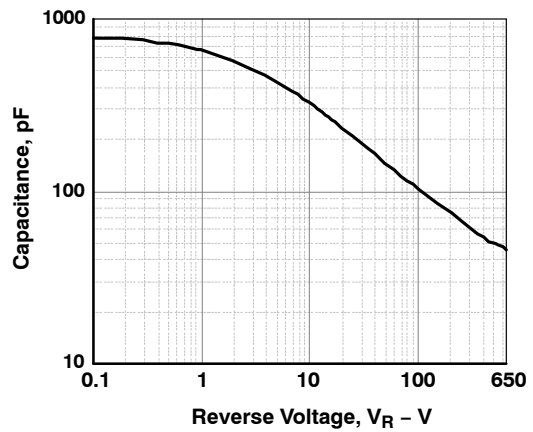

Figure 5. Capacitive Charge vs. Reverse Voltage

Figure 6. Capacitance vs. Reverse Voltage

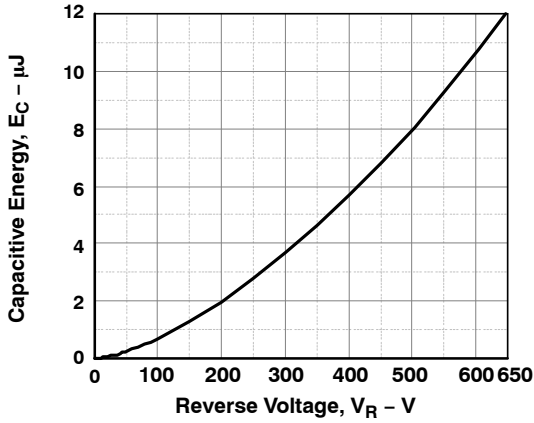## TYPICAL CHARACTERISTICS

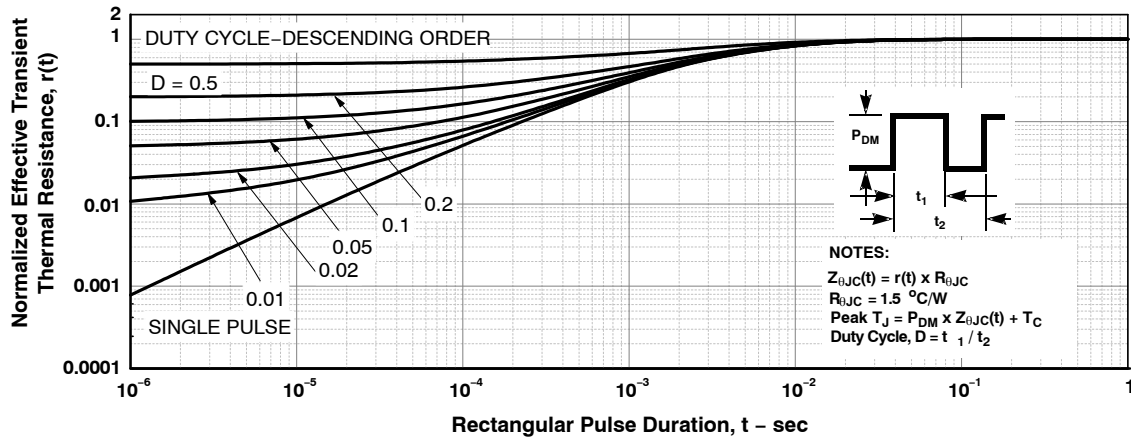(T$_J$ = 25°C UNLESS OTHERWISE NOTED)

Figure 7. Capacitance Stored Energy

Figure 8. Junction−to−Case Transient Thermal Response Curve

NOTES:
Z$_{\theta JC}$(t) = r(t) x R$_{\theta JC}$
R$_{\theta JC}$ = 1.5 °C/W
Peak T$_J$ = P$_{DM}$ x Z$_{\theta JC}$(t) + T$_C$
Duty Cycle, D = t$_1$ / t$_2$

TEST CIRCUIT AND WAVEFORMS

L = 0.5 mH
R < 0.1 Ω
V$_{DD}$ = 50 V
EAVL = 1/2LI2 [V$_{R(AVL)}$ / (V$_{R(AVL)}$ − V$_{DD}$)]
Q1 = IGBT (BV$_{CES}$ > DUT V$_{R(AVL)}$)
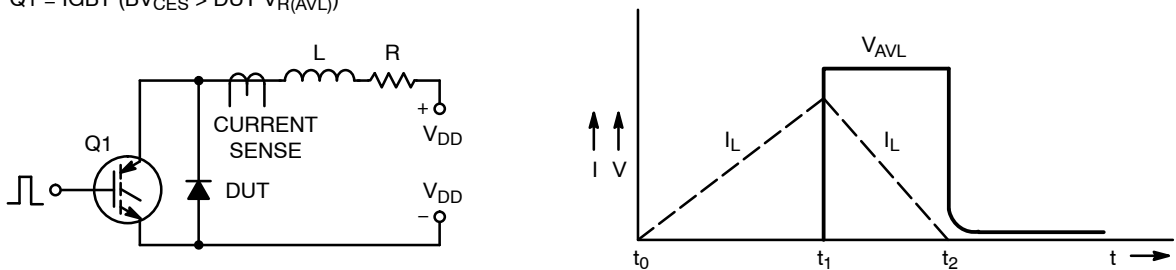
Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

D²PAK2 (TO−263−2L)
CASE 418BK
ISSUE O

DATE 02 AUG 2018

E
3
-A-
L1
D
L2
1
2
e
2X b
⊕ | 0.25 Ⓜ | B | A Ⓜ

A
-B-
c2
H
SEE DETAIL A

E1
3
D1
2
1
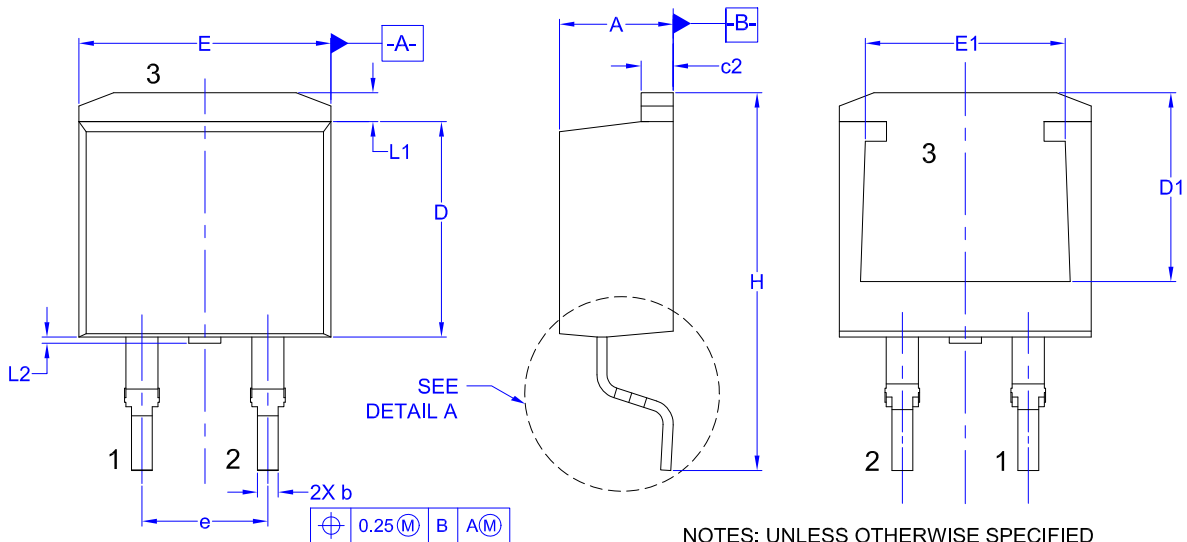
DETAIL A, ROTATED 90°
SCALE: 2X

GAUGE PLANE

M
c
B | 0.10 | ⌓
M
L
L3
A1
SEATING PLANE
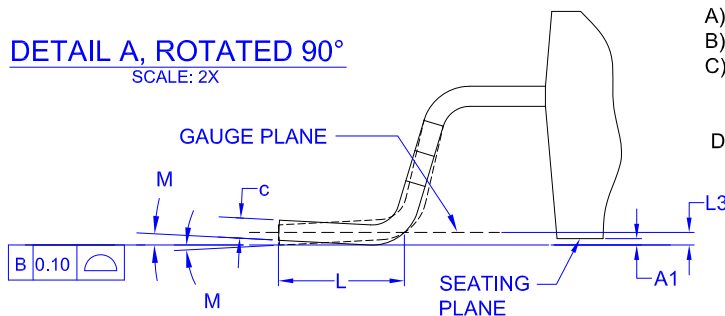
NOTES: UNLESS OTHERWISE SPECIFIED
A) ALL DIMENSIONS ARE IN MILLIMETERS.
B) REFERENCE JEDEC, TO-263, VARIATION AB.
C) DIMENSIONING AND TOLERANCING PER
DIMENSIONING AND TOLERANCING PER
ASME Y14.5 - 2009.
D) LANDPATTERN RECOMMENDATION PER IPC
TO254P1524X482-3N

GENERIC MARKING DIAGRAM*

XXXXXXXXG
AYWW
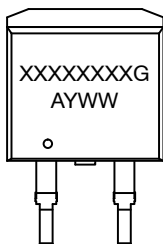
XXX = Specific Device Code
A   = Assembly Location
Y   = Year
WW = Work Week
G   = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot " ▪", may or may not be present. Some products may not follow the Generic Marking.

10.67
9.45
10.00
3.80
1.05
5.08
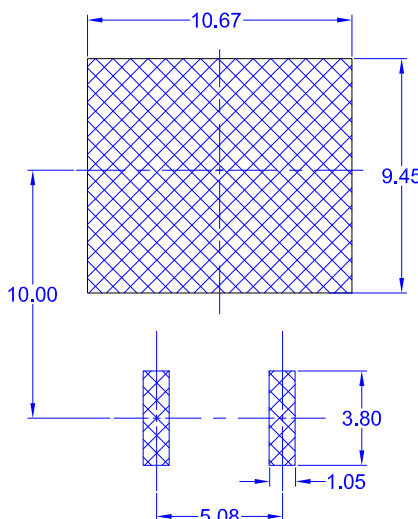
LAND PATTERN RECOMMENDATION
UNLESS NOTED, ALL DIMS TYPICAL

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.06	4.57	4.83
A1	0.00	0.10	0.25
b	0.51	0.81	0.99
c	0.30	0.407	0.74
c2	1.14	1.30	1.65
D	8.38	8.69	9.65
D1	7.30	7.80	8.30
E	9.65	10.16	10.67
E1	8.00	8.62	9.00
e	5.08 BSC		
H	14.60	15.35	15.88
L	1.78	2.54	2.79
L1	0.90	1.29	1.68
L2	0.00	0.15	0.25
L3	0.25 BSC		
M	0°	4°	8°

DOCUMENT NUMBER:	98AON93788G		
DESCRIPTION:	D²PAK2 (TO−263−2L)		PAGE 1 OF 1

ADDITIONAL INFORMATION